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2N5239, 2N5240 High-Voltage, Silicon N-P-N Transistors

MAXIMUM RATINGS, Absolute-Maximum Values:

	2N5239	2N5240	
V_{CBO}	300	375	V
$V_{CER(SUS)}$			
$R_{th} \leq 50 \Omega$	250	350	V
$V_{CEO(SUS)}$	225	300	V
V_{EBO}	6		V
I_C	5		A
I_B	2		A
P_T			
$T_C \leq 25^\circ\text{C}$ and $V_{CE} \leq 125\text{ V}$	100		W
$T_C \leq 25^\circ\text{C}$ and $V_{CE} \leq 125\text{ V}$	See Fig. 1		
$T_C > 25^\circ\text{C}$ and $V_{CE} > 125\text{ V}$	See Fig. 1		
T_{stg}, T_J	-65 to 200		$^\circ\text{C}$
T_C			
At distance $\geq 1/32$ in. (0.8 mm) from seating plane for 10 s max.	230		$^\circ\text{C}$

* In accordance with JEDEC registration data

ELECTRICAL CHARACTERISTICS, At Case Temperature (T_C) = 25°C unless otherwise specified

CHARACTERISTIC	TEST CONDITIONS				LIMITS				UNITS
	VOLTAGE V dc		CURRENT A dc		2N5239		2N5240		
	V _{CE}	V _{BE}	I _C	I _B	Min.	Max.	Min.	Max.	
I _{CEO}	200			0	—	5	—	2	mA
I _{CEV}	300	-1.5			—	4	—	—	
	375	-1.5			—	—	—	2	
(T _C = 150° C)	300	-1.5			—	5	—	3	
I _{EBO} (V _{EB} = 5 V)			0		—	5	—	1	V
(V _{EB} = 6 V)			0		—	20	—	20	
V _{FBO}				0.02	6	—	6	—	V
V _{CEO(SUS)} ^a			0.2 ^b		225	—	300	—	
V _{CER(SUS)} ^a (R _{th} ≤ 50 Ω)			0.2 ^b		250	—	350	—	
h _{FE}	10		0.4 ^b		20	80	20	80	V
	10		2 ^b		20	80	20	80	
	10		4.5 ^b		5	—	5	—	
V _{BE}	10		2 ^b		—	3	—	3	V
V _{CE(sat)}			2 ^b	0.25	—	2.5	—	2.5	
			4.5 ^b	1.125	—	5	—	5	
I _{SH} (t = 1 s)	125				0.8	—	0.8	—	A
h _{FE} (f = 1 MHz)	10		0.2		2	—	2	—	MHz
h _{FE} (f = 1 kHz)	10		4		20	—	20	—	
f _T	10		0.2		2	—	2	—	
C _{obo} (f = 1 MHz)	10 ^c		0		—	250	—	250	pF
R _{θJC}					—	1.75	—	1.75	°C/W

* In accordance with JEDEC registration data.

^a CAUTION: The sustaining voltages $V_{CEO(SUS)}$ and $V_{CER(SUS)}$ MUST NOT be measured on a curve tracer.

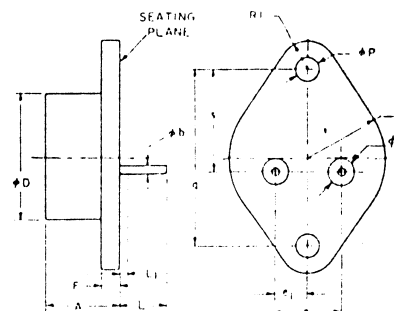
^b Pulsed; pulse duration $\leq 350\text{ }\mu\text{s}$, duty factory $\leq 2\%$.

^c V_{CB} value.

Dimensional Outlines

TO-204AA

200-mil diameter pin isolation



Notes:

1: ϕb applies between L_1 and L . Diameter is uncontrolled in L_1 .

SYMBOL	INCHES		MILLIMETERS		N
	MIN.	MAX.	MIN.	MAX.	
A	0.250	0.450	6.35	11.35	
ϕb	0.038	0.043	0.96	1.092	
ϕb_1	0.200 NOM.		5.08 NOM.		
ϕD	—	0.875	—	22.22	
e	0.420	0.440	10.67	11.17	
e_1	0.205	0.225	5.21	5.71	
F	0.060	0.135	1.53	3.42	
L	0.312	0.500	7.93	12.70	
L_1	—	0.050	—	1.27	
ϕP	0.151	0.161	3.83	4.089	
q	1.177	1.197	29.50	30.40	
R	0.495	0.525	12.58	13.33	
R_1	0.131	0.183	3.33	4.77	
s	0.655	0.675	16.64	17.14	

2: These dimensions should be measured at point in. (1.270 mm) to 0.055 in. (1.397 mm) below plane. When gage is not used, measurement made at seating plane.